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Development of High-Resolution Compton Cameras Based on Si/CdTe Imaging Detectors

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Compton Camera

Energy band from 100 keV to 10 MeV

Compton scattering is dominant over all other interactions of a photon with detector material.

Promising sub-MeV/MeV gamma-ray imaging spectrometer for

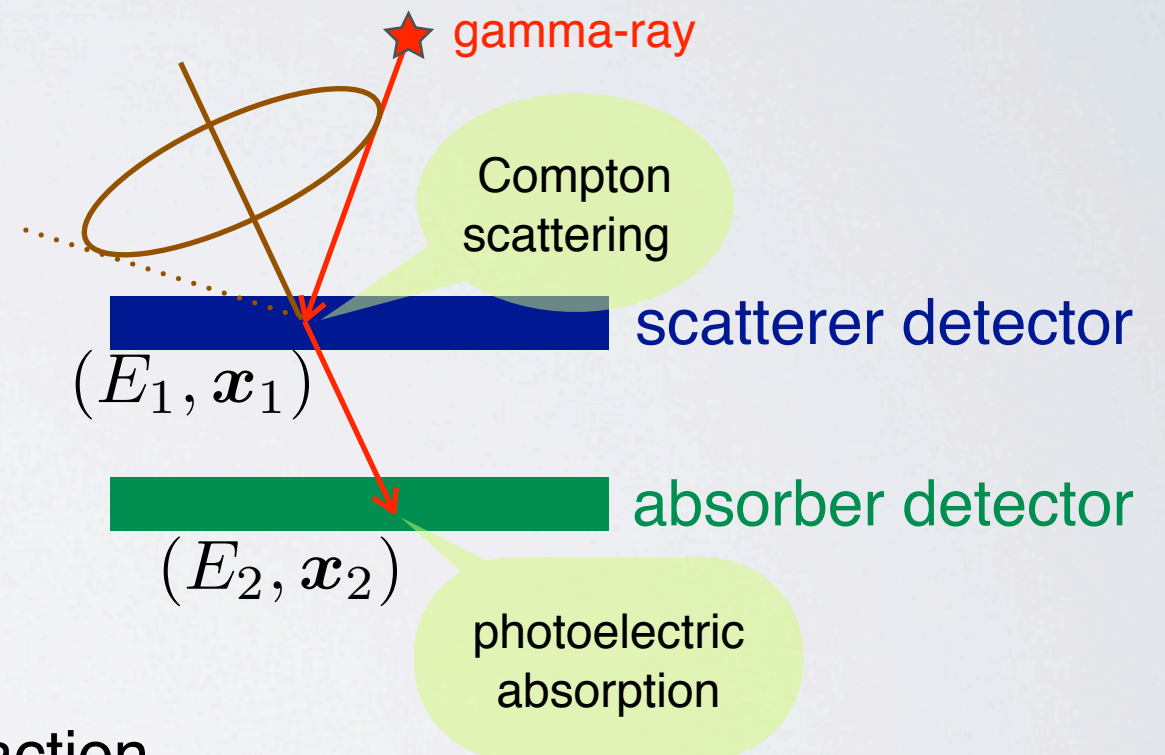
- Astrophysical observation
- Medical imaging
- Nondestructive inspection
- Search for radioactive isotopes

Energy and direction of the incident photon are determined by Compton kinematics.

E_i : Energy deposited

\mathbf{x}_i : Position of an interaction

$$E = E_1 + E_2, \quad \cos \theta = 1 - m_e c^2 \left(\frac{1}{E_2} - \frac{1}{E_1 + E_2} \right)$$



Accurate measurement of energy and position is important to obtain high angular/spatial resolution.

Advantage of Si/CdTe

Semiconductor imaging detectors are the most suitable.

High Energy/Position Resolution

1) Si detector as the scatterer [Low-Z: $Z=14$]

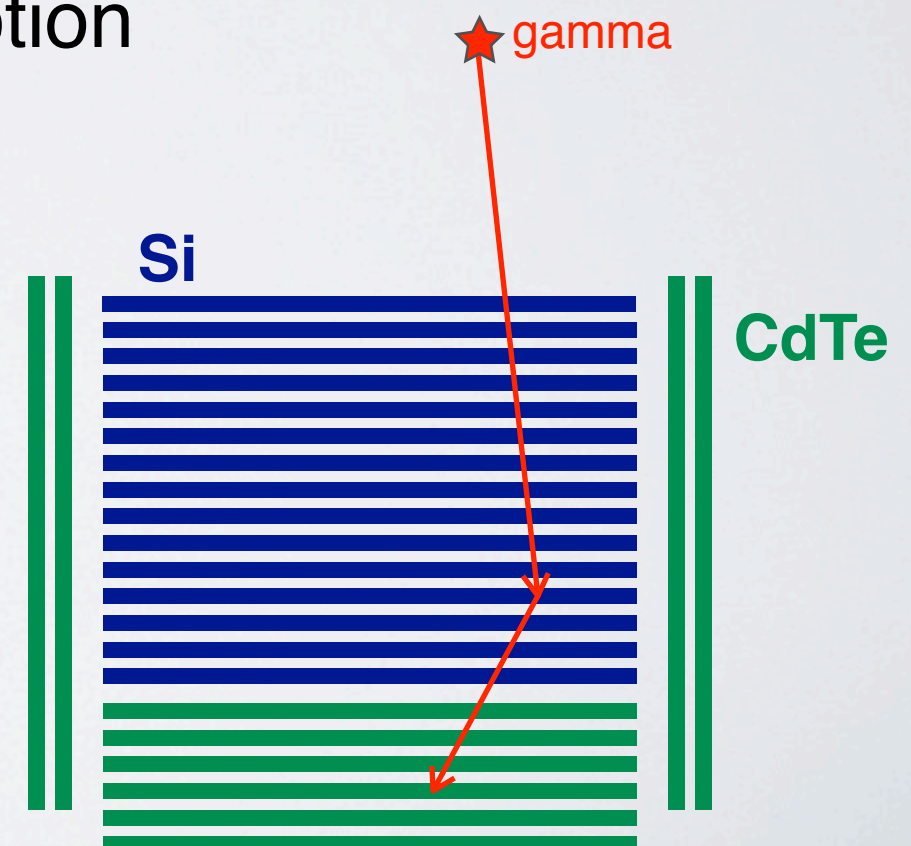
- High probability of Compton scattering
- Small Doppler broadening effect (by target electron momentum)

2) CdTe detector as the absorber [High-Z: $Z=48,52$]

- Large cross section of photoelectric absorption
- High density (5.85 g/cm^3)
- Schottky diode electrode configuration
reduced low-energy tail (high bias voltage)
Takahashi+ (2002)

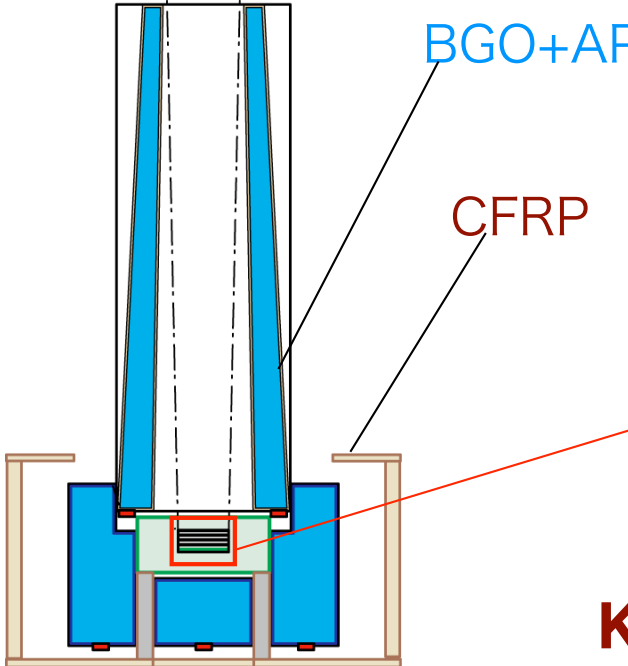
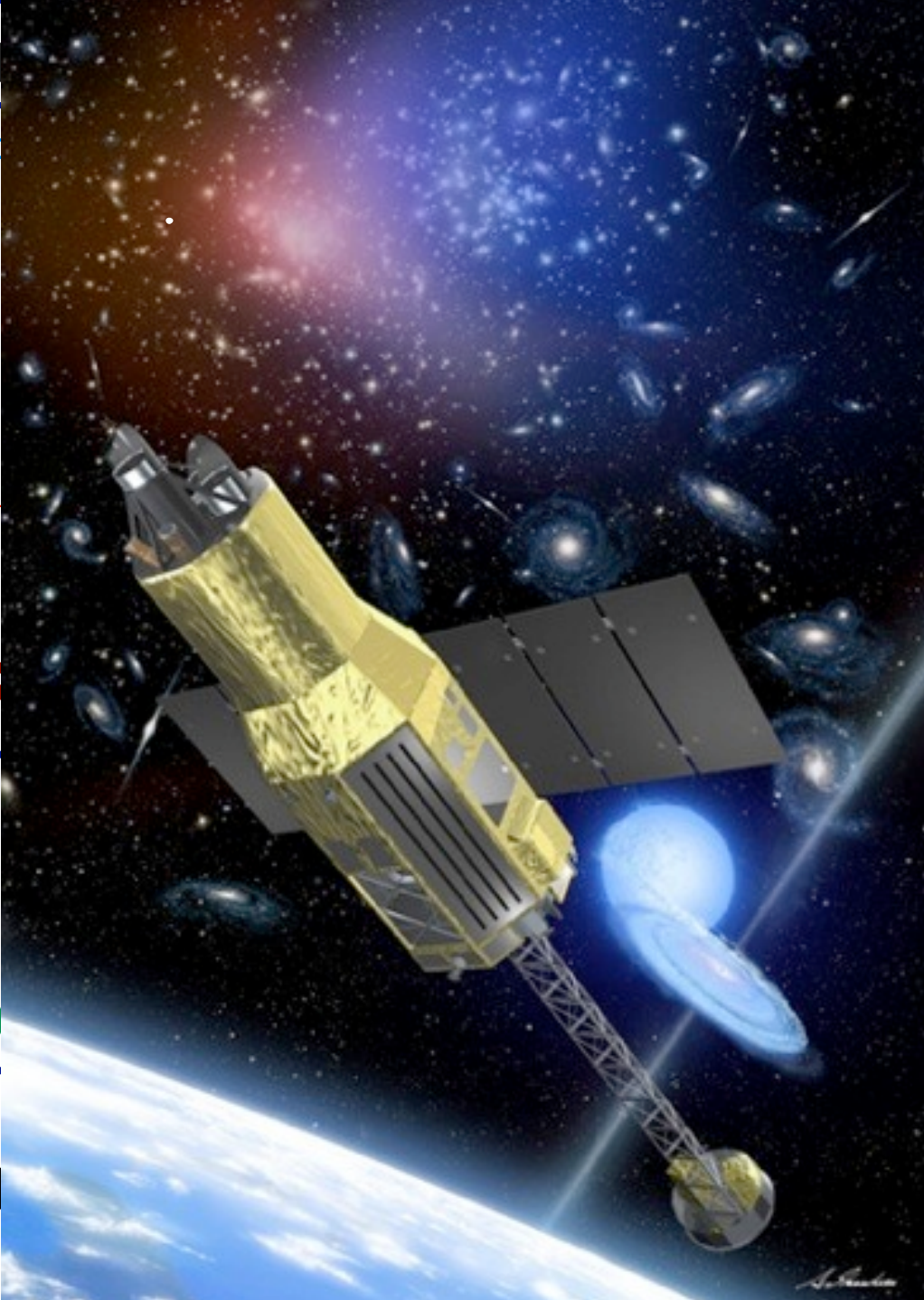
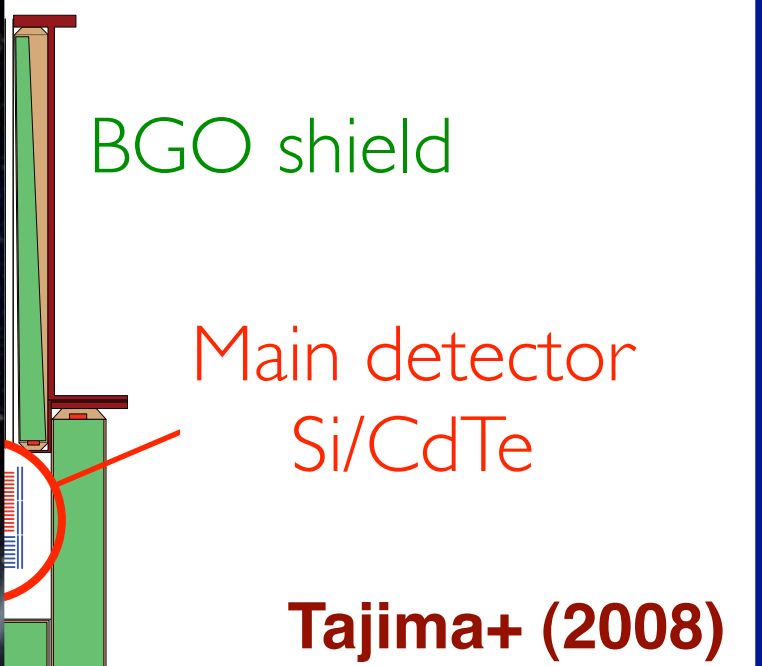
Design of Si/CdTe Compton cameras

- ✓ Combination of Si and CdTe detectors with high resolution
- ✓ Many-layer stack structure with small pitch



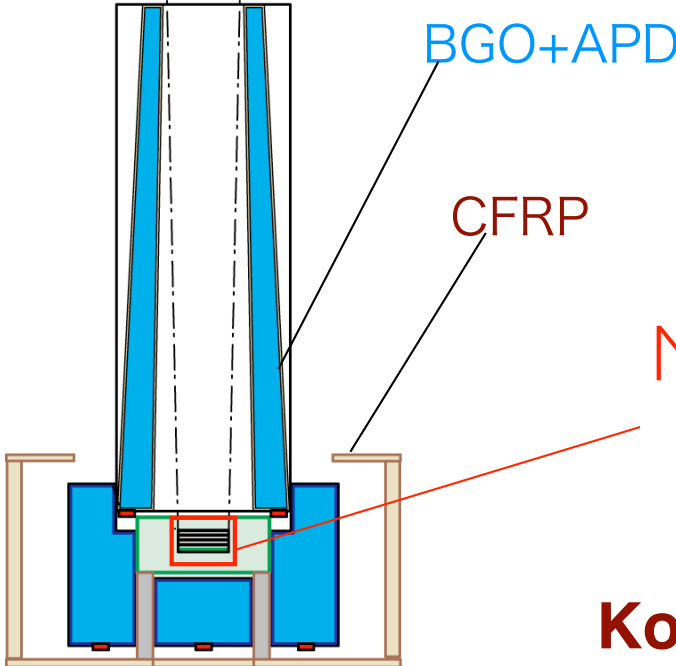
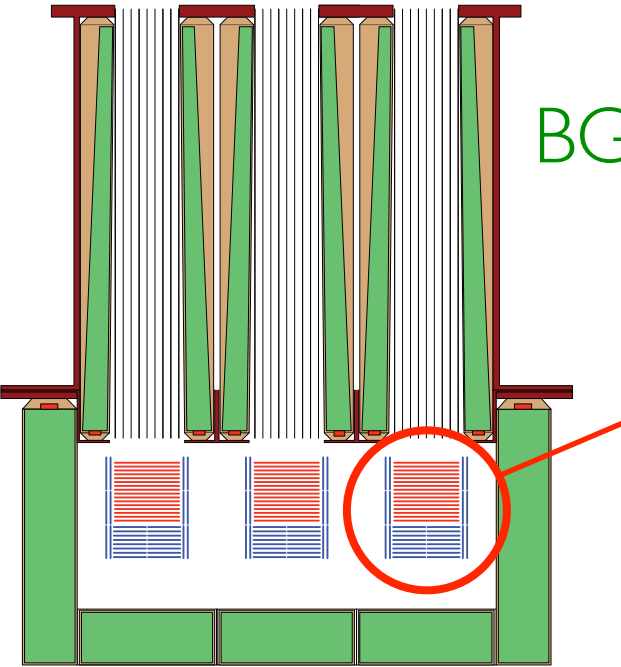
ASTRO-H X-ray Observatory

ASTRO-H is the next X-ray satellite led by JAXA, scheduled for launch in 2014. (Takahashi+ 2010)

<p>Hard X-ray Image</p>  <p>BGO+APD CFRP</p>		<p>Soft X-ray Detector (SGD)</p>  <p>BGO shield Main detector Si/CdTe</p> <p>Tajima+ (2008)</p>
<p>4-layer Si-DSD 32.0 x 32.0 x 0.5 mm, 250</p> <p>1-layer CdTe-DSD 32.0 x 32.0 x 0.75 mm, 250</p>		<p>1.5 mm thick, 32 layers 0.5 mm thick, 1.5 mm, 2 layers at each sides CC unit x 6 CC</p>
<ul style="list-style-type: none"> • 5 - 80 keV • Focal plane detector of HXIS mirror 		<p>Compton telescope</p>

ASTRO-H X-ray Observatory

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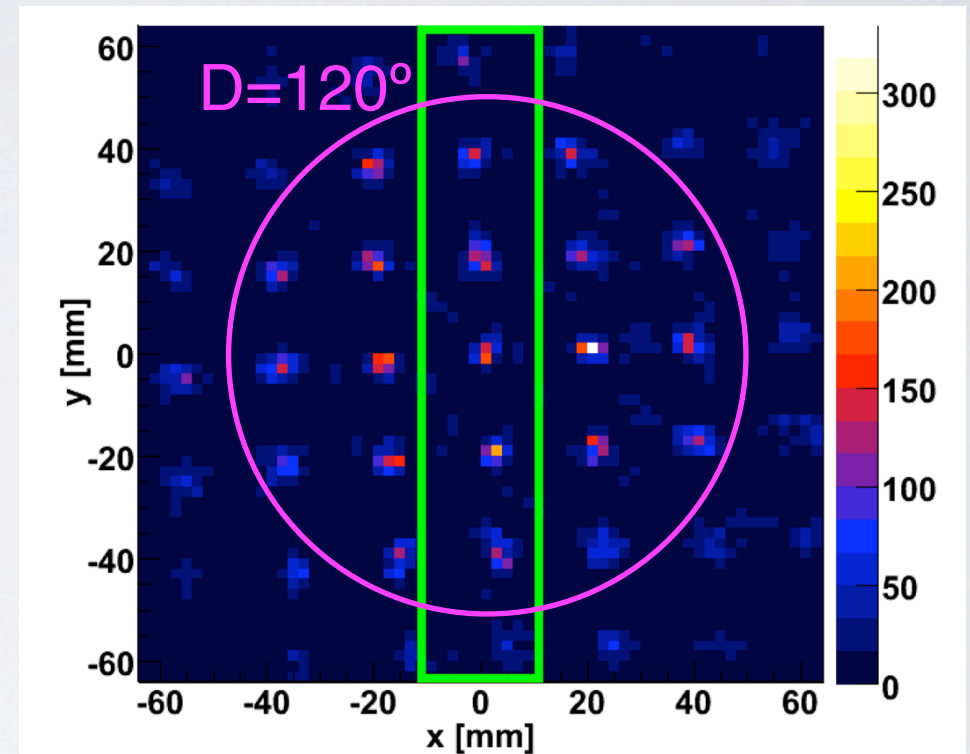
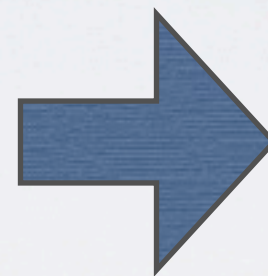
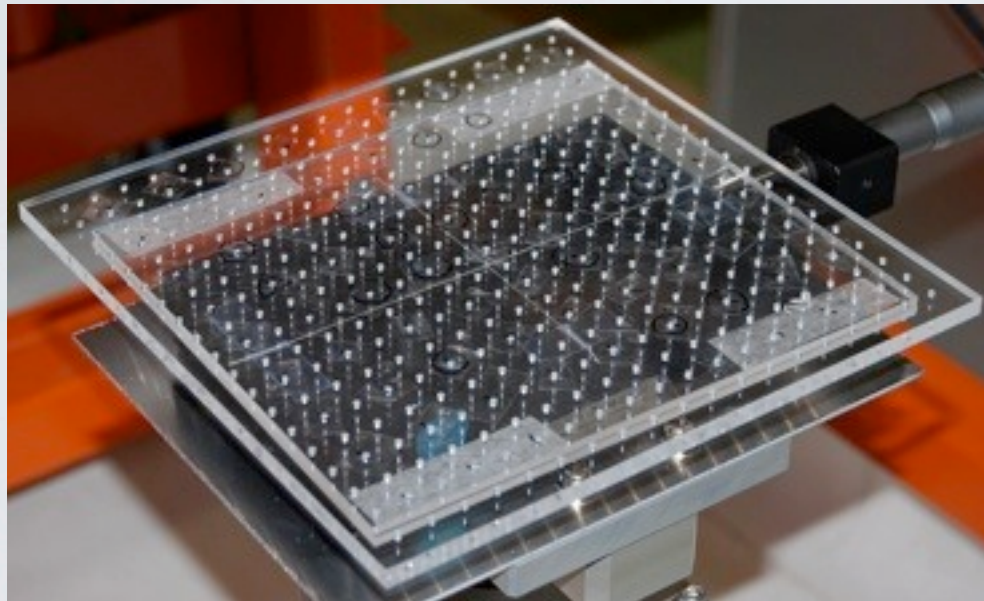
Hard X-ray Imager (HXI)	Soft Gamma-ray Detector (SGD)
 <p>BGO+APD</p> <p>CFRP</p> <p>Main detector Si/CdTe</p> <p>Kokubun+ (2008)</p>	 <p>BGO shield</p> <p>Main detector Si/CdTe</p> <p>Tajima+ (2008)</p>
<p>4-layer Si-DSD 32.0 x 32.0 x 0.5 mm, 250 um strip pitch</p> <p>1-layer CdTe-DSD 32.0 x 32.0 x 0.75 mm, 250 um strip pitch</p>	<p>Si-Pad 0.6 mm thick, 32 layers</p> <p>CdTe-Pad 0.75 mm thick, 8 layers at bottom, 2 layers at each sides</p> <p>13321 channels/CC unit x 6 CC</p>
<ul style="list-style-type: none"> • 5 - 80 keV • Focal plane detector of Hard-X-ray super mirror 	<ul style="list-style-type: none"> • 10 - 600 keV • Narrow-FOV Compton telescope

Results from Prototypes *Compton Imaging*

Takeda+ (2009)
collaboration with
Gunma Univ. & JAEA

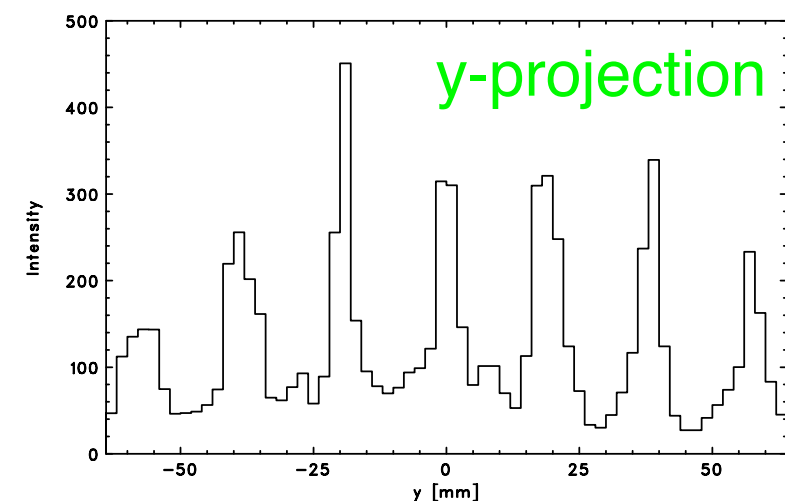
1-layer Si + 4-layer CdTe

Multiple point sources



- Liquid ^{131}I source (364 keV)
- Grid with a gap of 20 mm
- Distance of 60 mm from the camera top

- 1 mm position accuracy (distance: 60 mm)
- $\text{FOV} > 120^\circ$



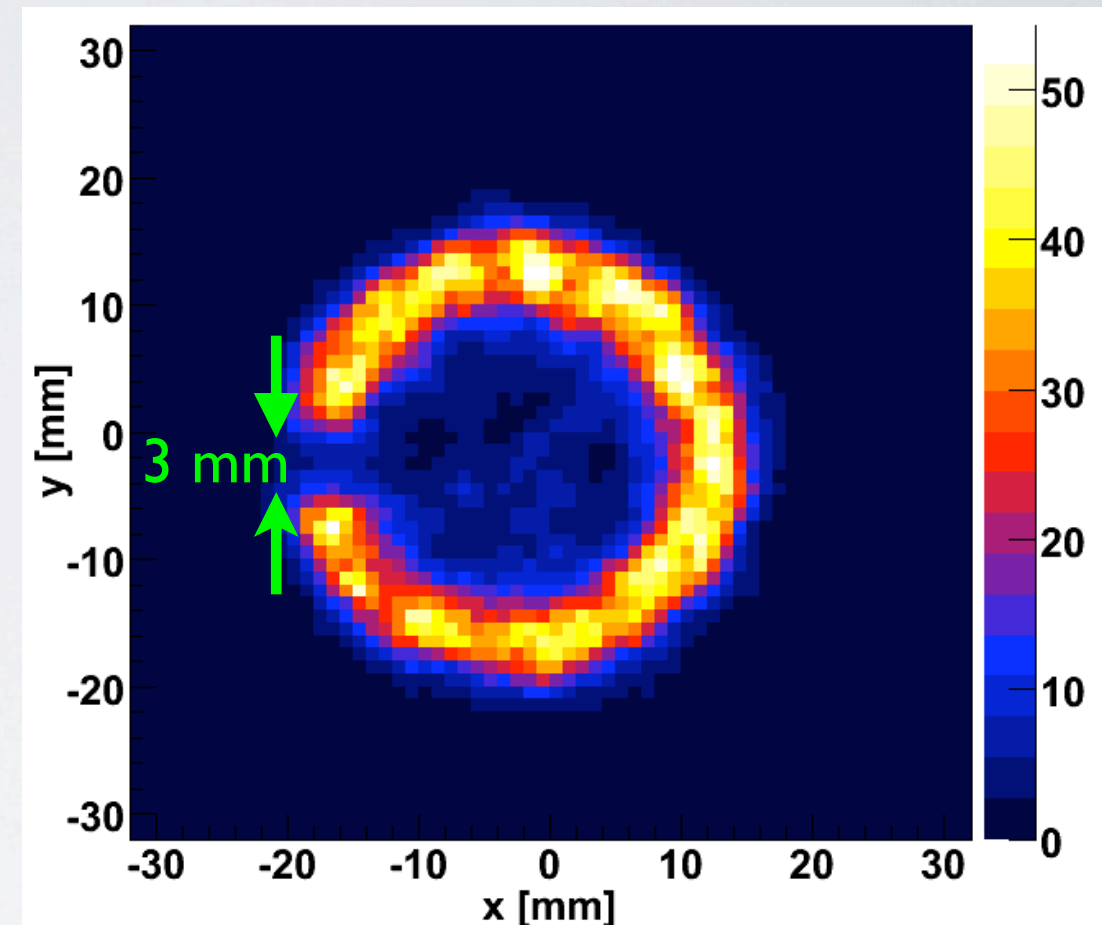
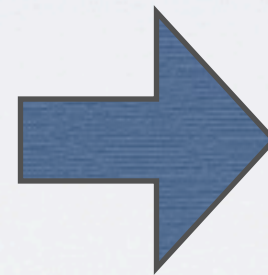
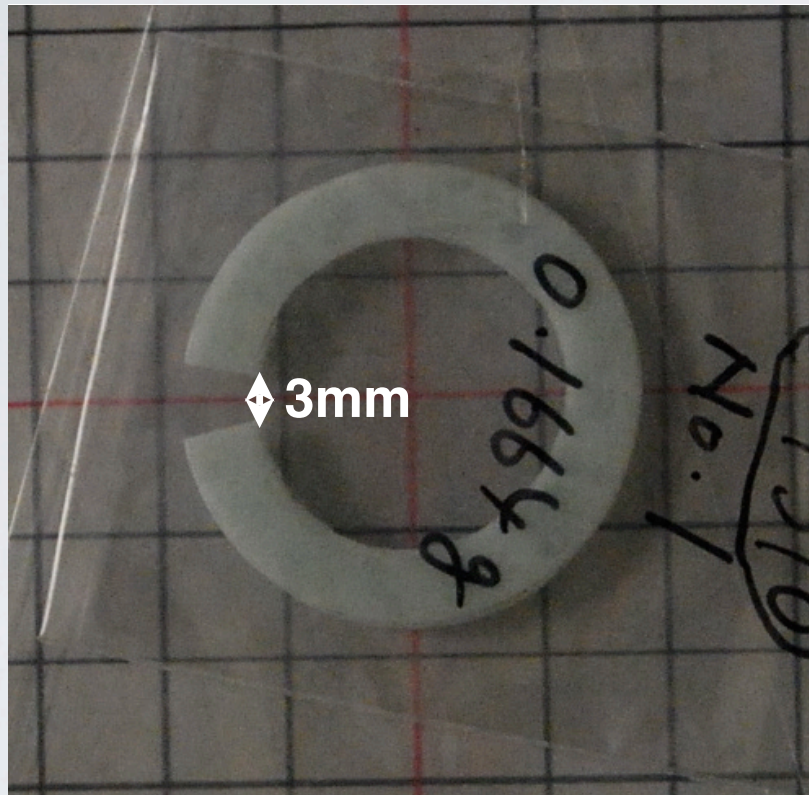
Results from Prototypes

Compton Imaging

Takeda+ (2009)
collaboration with
Gunma Univ. & JAEA

1-layer Si + 4-layer CdTe

Extended sources



- Liquid ^{131}I source (364 keV)
- reverse “C” shape
- Distance of 30 mm from the top

- Imaging of diffuse emission is well performed.
- Spatial resolution is better than 3 mm. (distance: 30 mm)

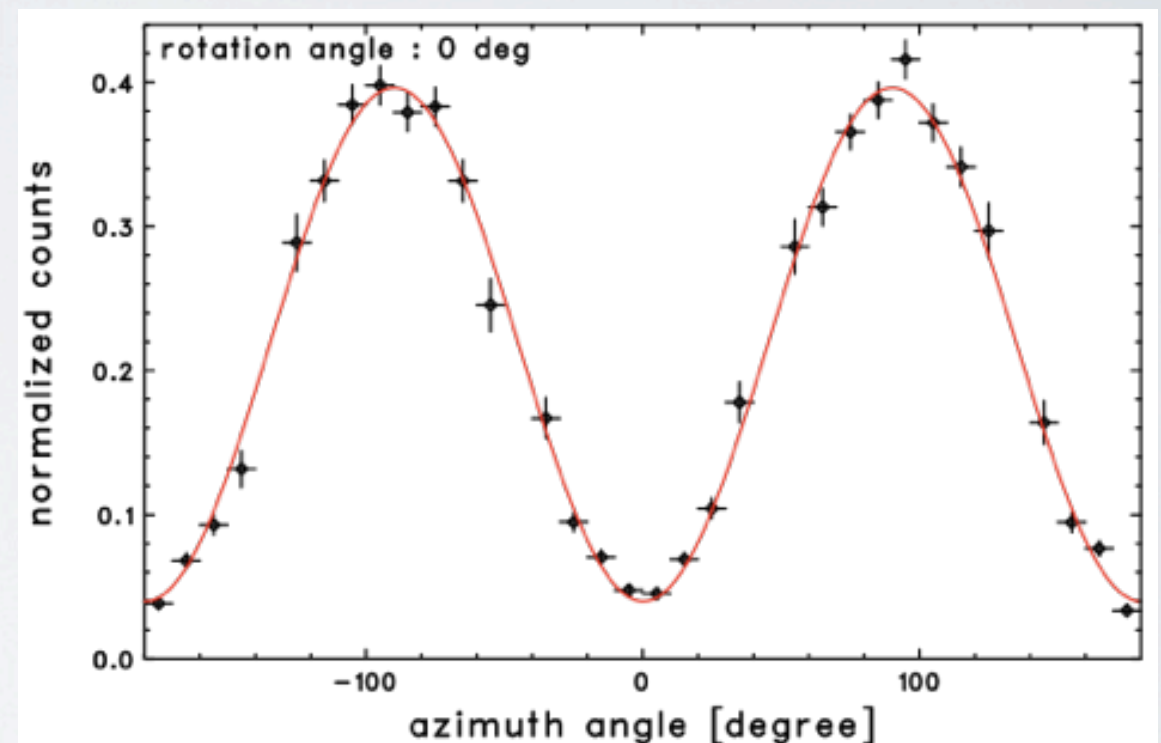
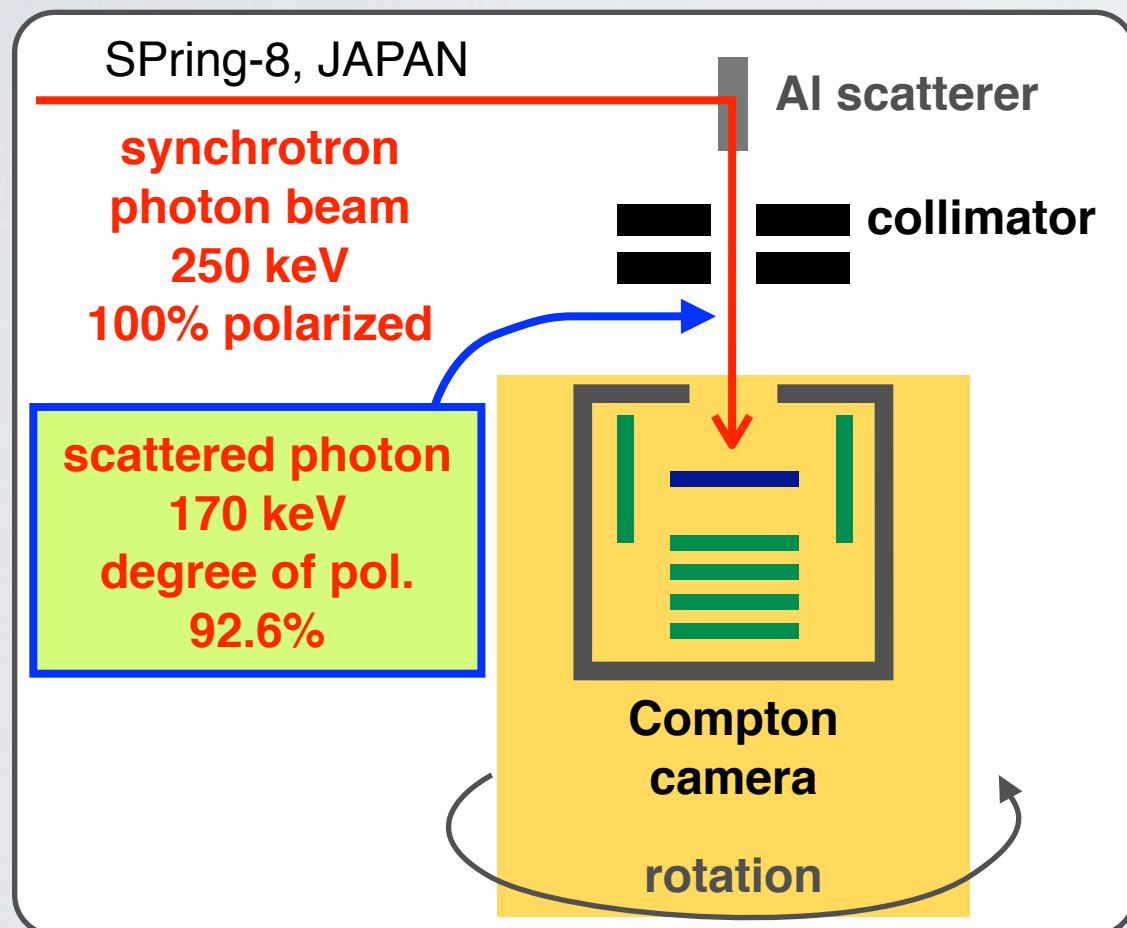
Results from Prototypes

High-Precision Polarimetry

Principle: anisotropy of the azimuth angle distribution of Compton scattering

Advantage over conventional Compton polarimeters

- High precision measurement of the azimuth angle
- Restrict the incident direction of photons (Background rejection)



Modulation factor = 0.82 ± 0.01

Polarization angle = $0.2^\circ \pm 0.4^\circ$

- The measured modulation factor agrees with the theoretical value.
 $0.83 = 0.926 \times 0.90$ (modulation factor for 100% polarized beam)
- Polarization angle is determined to a precision of 1° .

Takeda+ (2010)

Strategy for Higher Performance

Two important performance keys:

1) Angular/Spatial Resolution

	Energy	Position
Precise measurement	New ADC-included low-noise readout ASICs VATA 450/460/461	New fine-pitch CdTe double-sided strip detectors
Detailed data reduction	Efficient calibration method using Compton events	Depth sensing & inter-strip events using multi-strip information

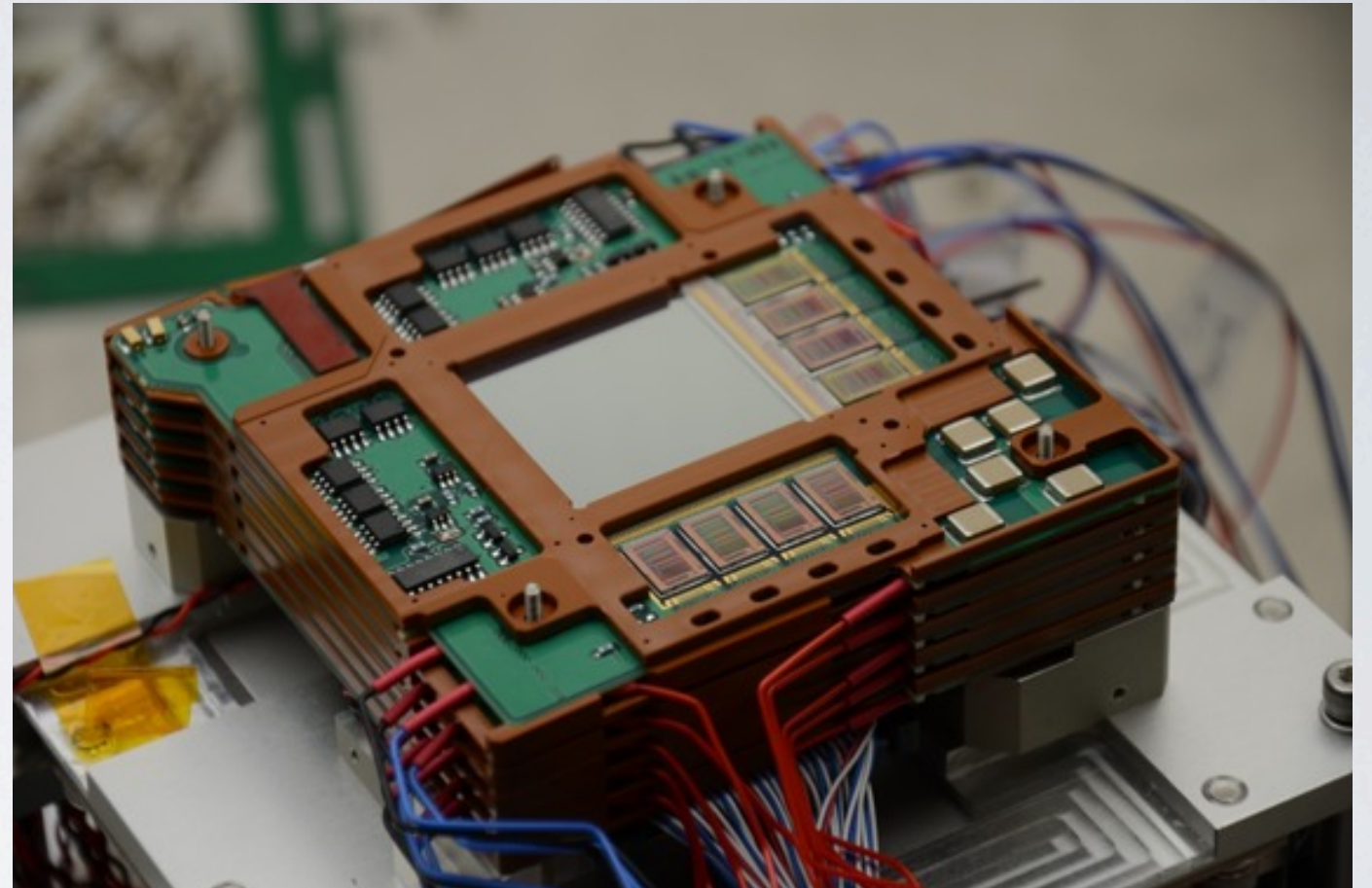
2) Detection Efficiency

- Large-area & multi-layer stacking of double-sided strip detectors
- Modular design → flexible & scalable configuration

New Camera Module

- ✓ Stack of DSDs with high energy/position resolutions
- ✓ Highly modular design
- ✓ The detector configuration is flexible and scalable for specific applications.
Example: 1 Si + 4 CdTe

assembled by MHI



Common spec.	DC-coupled floating readout with VATA 460/461 Active area: 3.2 x 3.2 cm ² 128 strips in each side with 250-um pitches
Si-DSD	ΔE : 1.5 keV at 60 keV (FWHM) Thickness: 500 um Hamamatsu
CdTe-DSD	$\Delta E/E$: 1% at 500 keV (FWHM) Thickness: 750 um ACRORAD

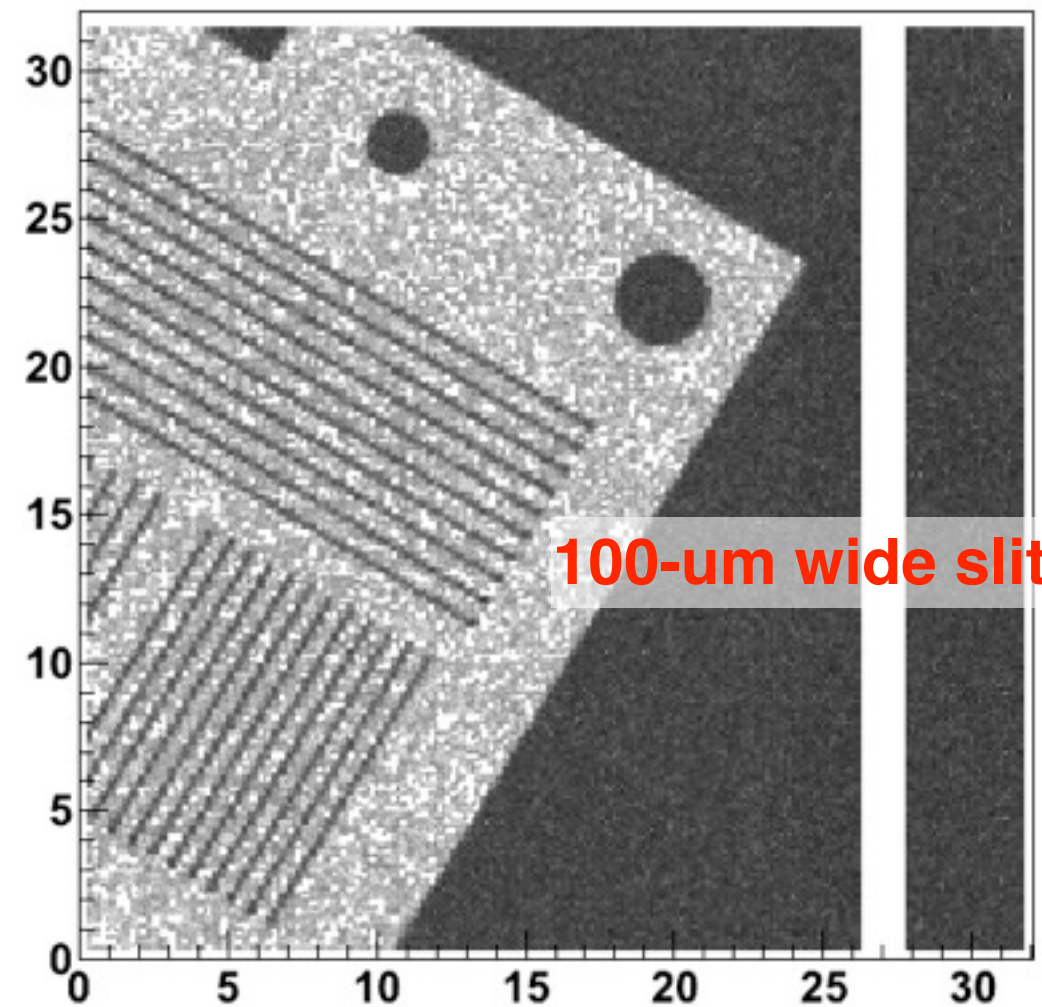
250-um Pitch CdTe-DSD

Key detector of the Si/CdTe system

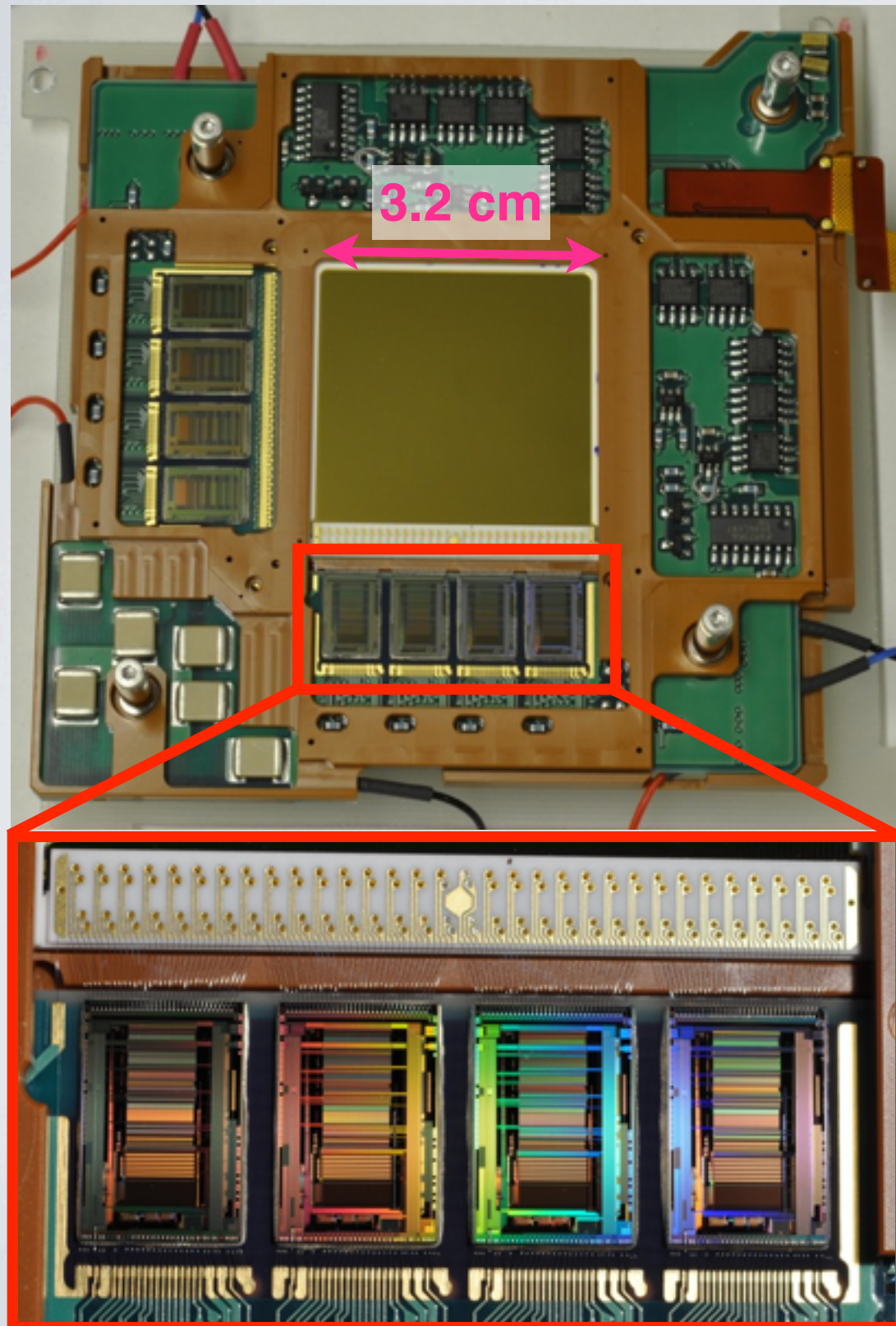
Watanabe+ (2009), Ishikawa+ (2010)

Shadow image (28-33 keV)

550-um thick tungsten mask



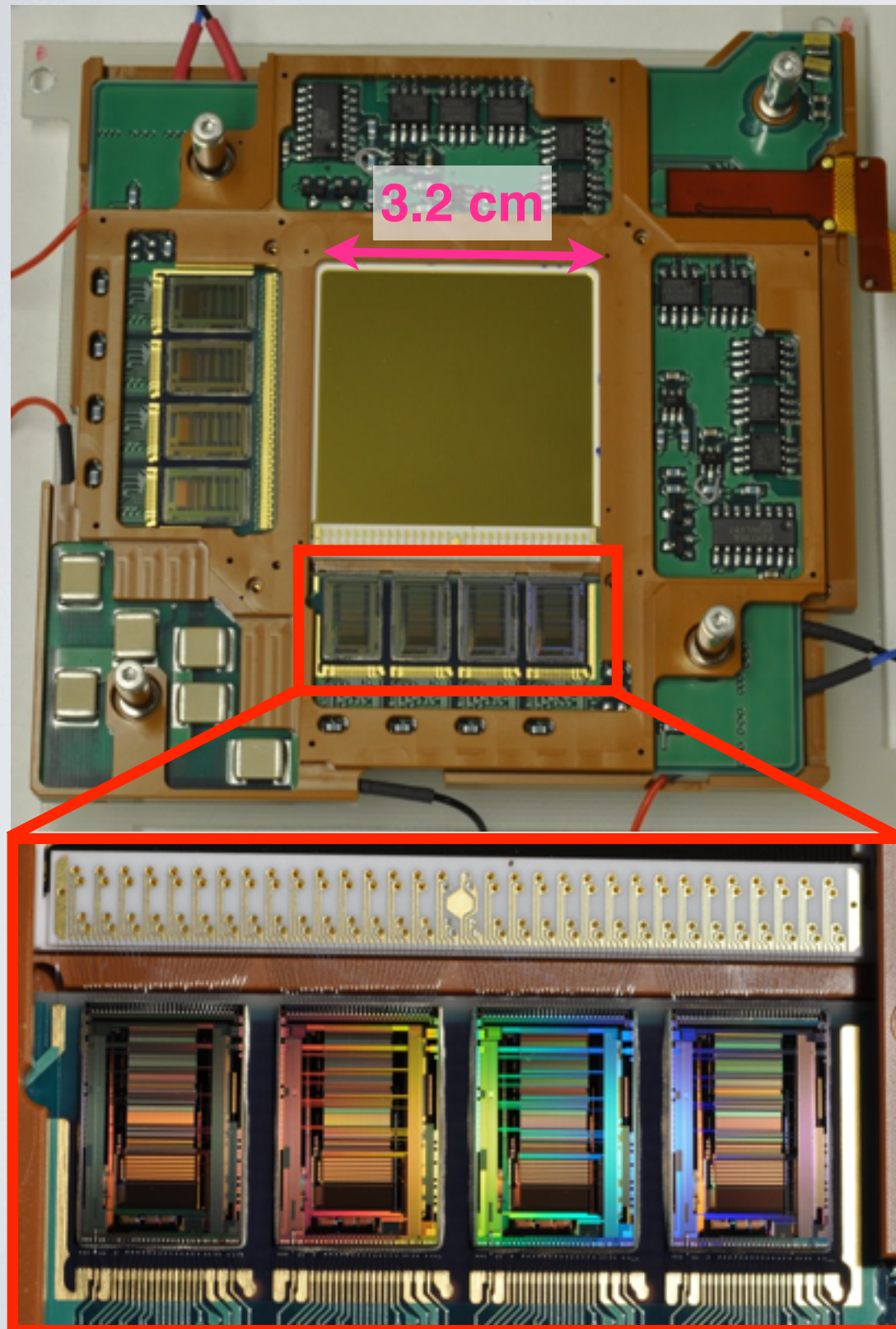
3.2 cm



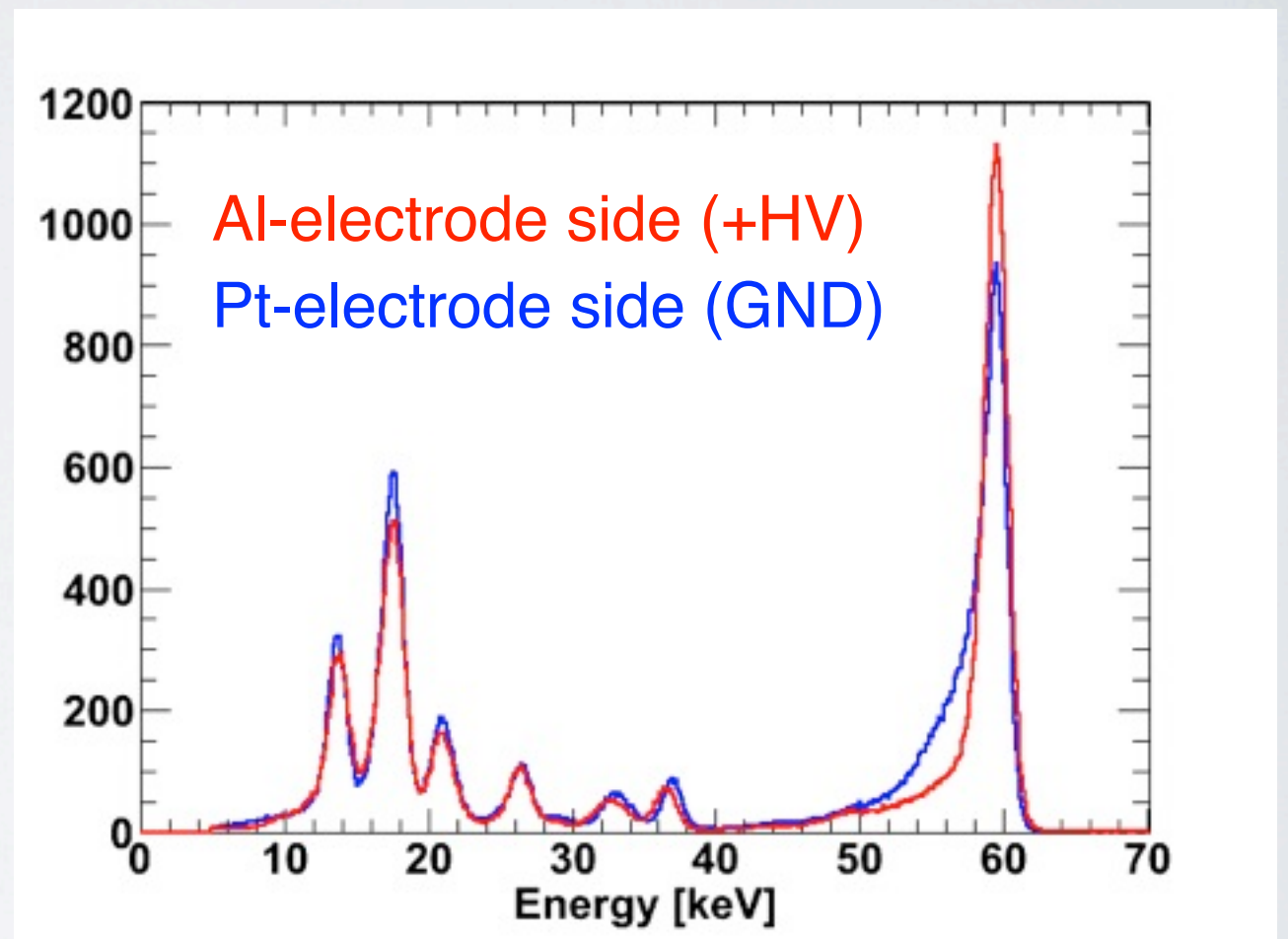
250-um Pitch CdTe-DSD

Key detector of the Si/CdTe system

Watanabe+ (2009), Ishikawa+ (2010)



Am-241 spectrum



Applied bias: 250 V

ΔE : 1.7-1.9 keV at 60 keV (FWHM)

Low threshold: 5 keV

Detector Response

For scientific applications (spectral fitting, image deconvolution,...), correct understanding of the detector response is required.

To handle complex response of the Si/CdTe Compton camera, we have developed a full Monte Carlo simulator. (Odaka+ 2010)

Particle tracking
(Geant4)

Energy deposited in the detector (E, \mathbf{x})

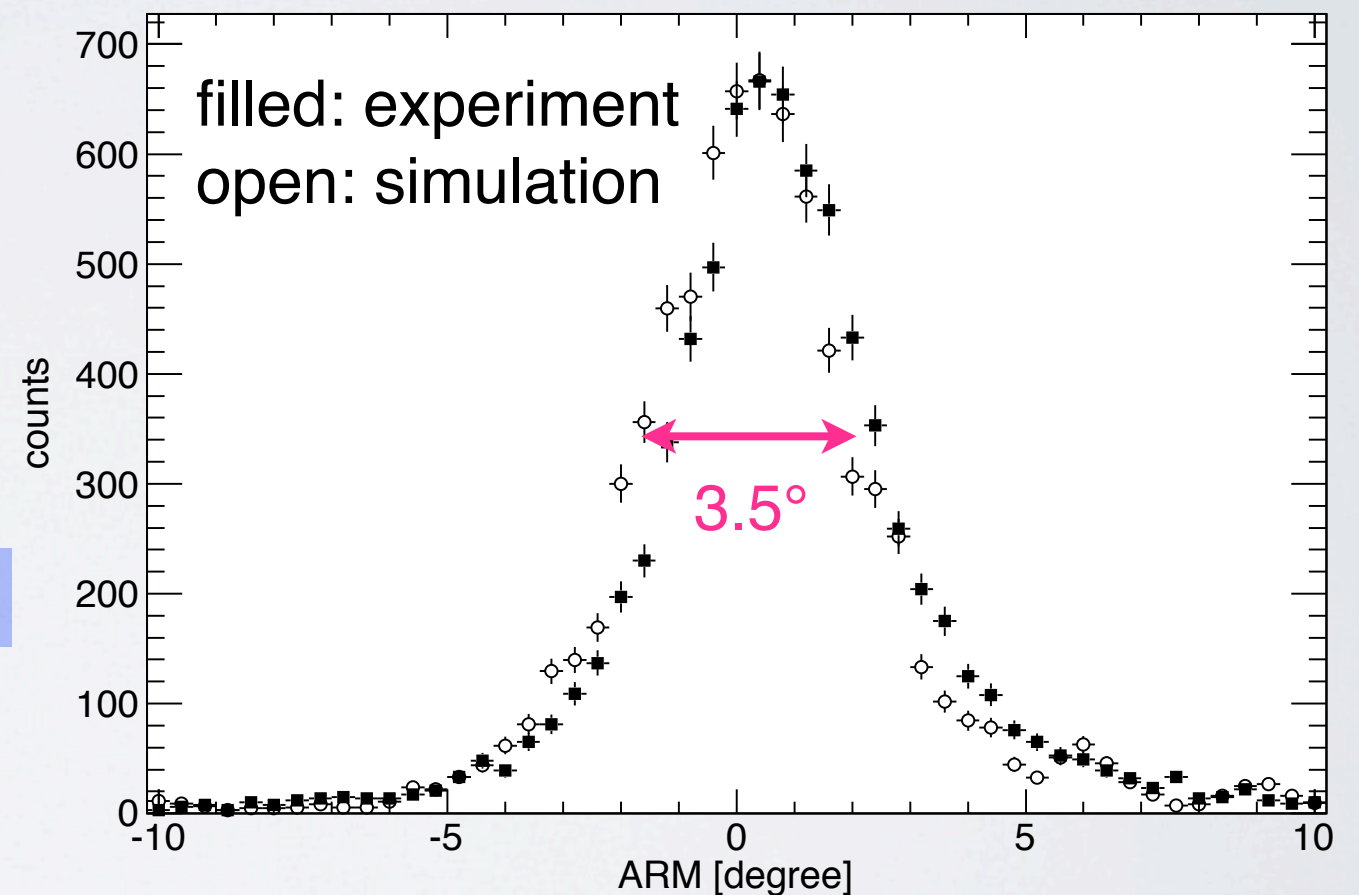
Device
charge transport/diffusion

Signal pulse height from readout channels

Signal processing
Data acquisition

Data output

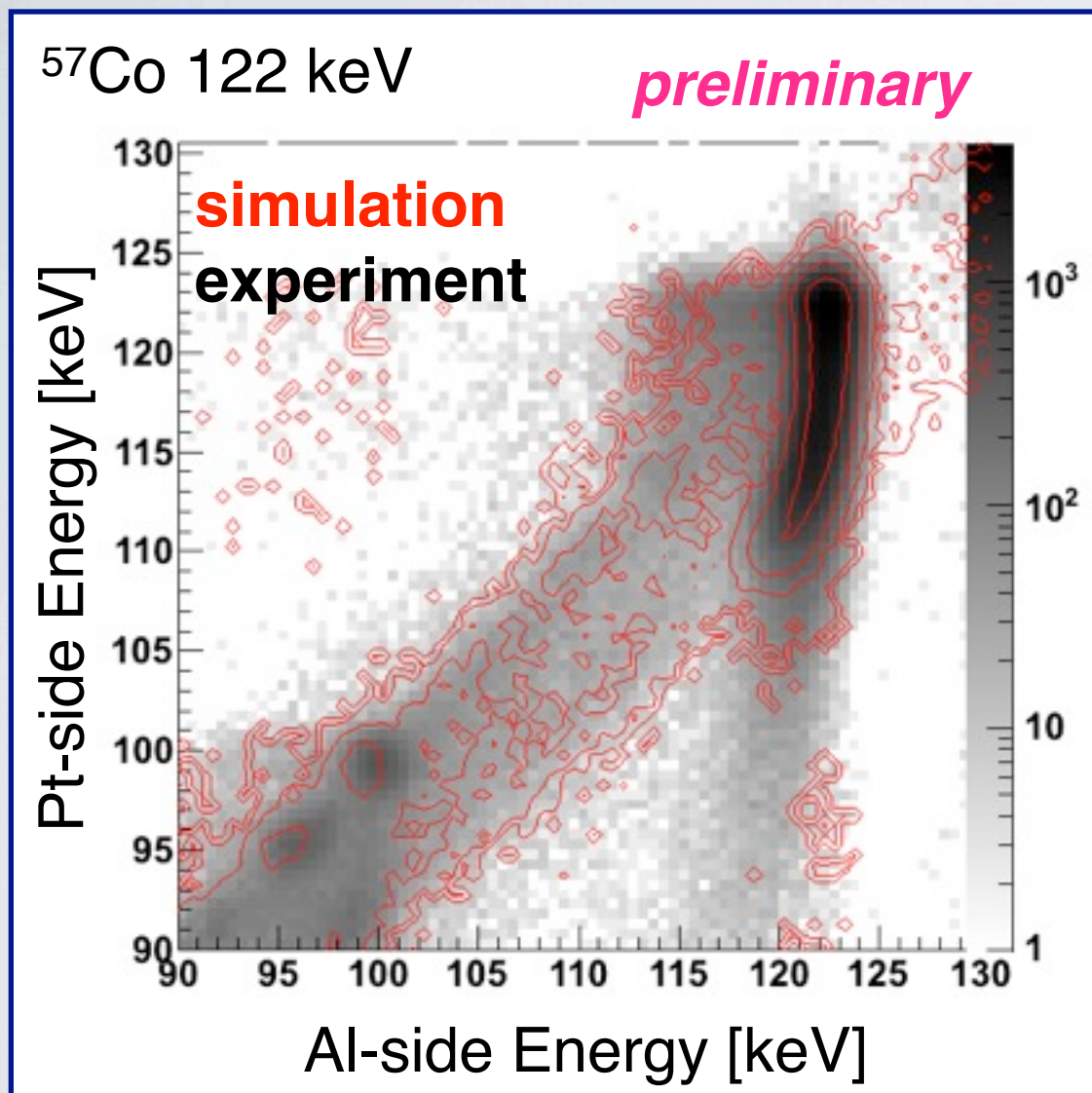
same format as the real experimental data



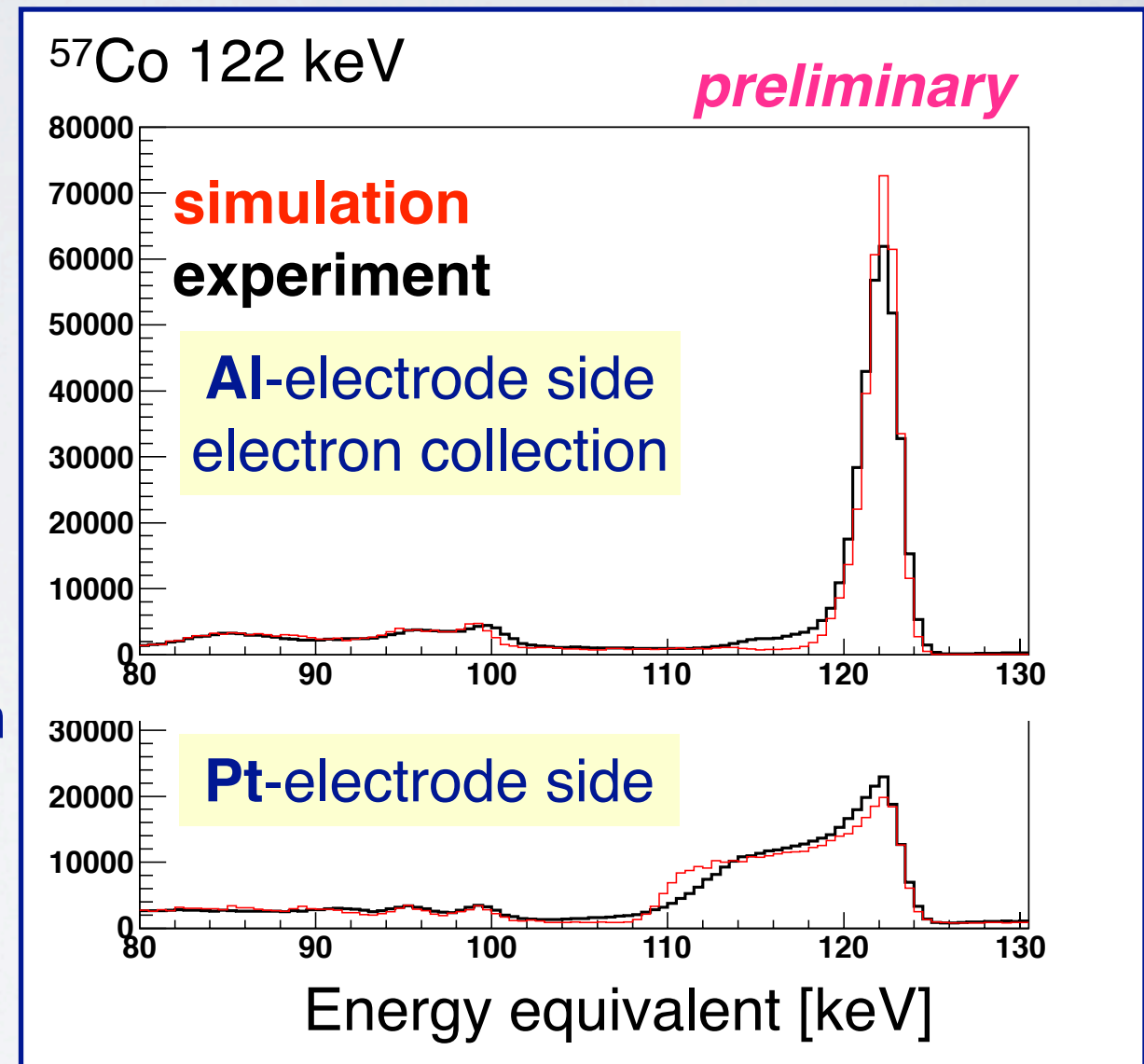
Angular response (ARM) at 356 keV
Good agreement with an experimental result from the prototype

Response of CdTe

Complex detector response due to incomplete charge collection
(small mobility-lifetime product of hole)



projection

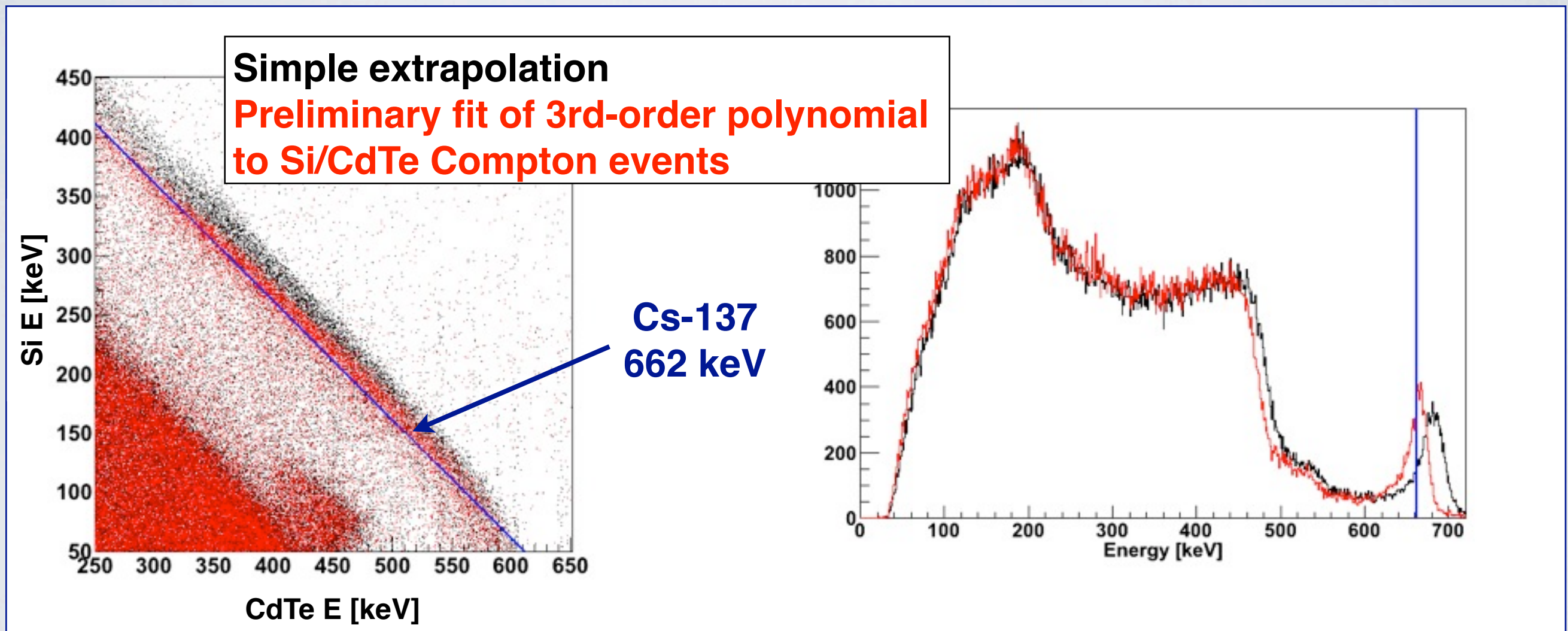


- We are now investigating inter-strip events, which can produce charge-shared events and/or low-energy tail structure.
- Polarization of CdTe is also an important issue. We established long-term stability at the ASTRO-H operation temperature, -20°C . (Sato+ 2010)

Calibration

High resolution detectors require accurate calibrations!
Calibration using gamma-ray lines is not realistic at high energies for Si detectors because photoelectric absorption hardly occurs.

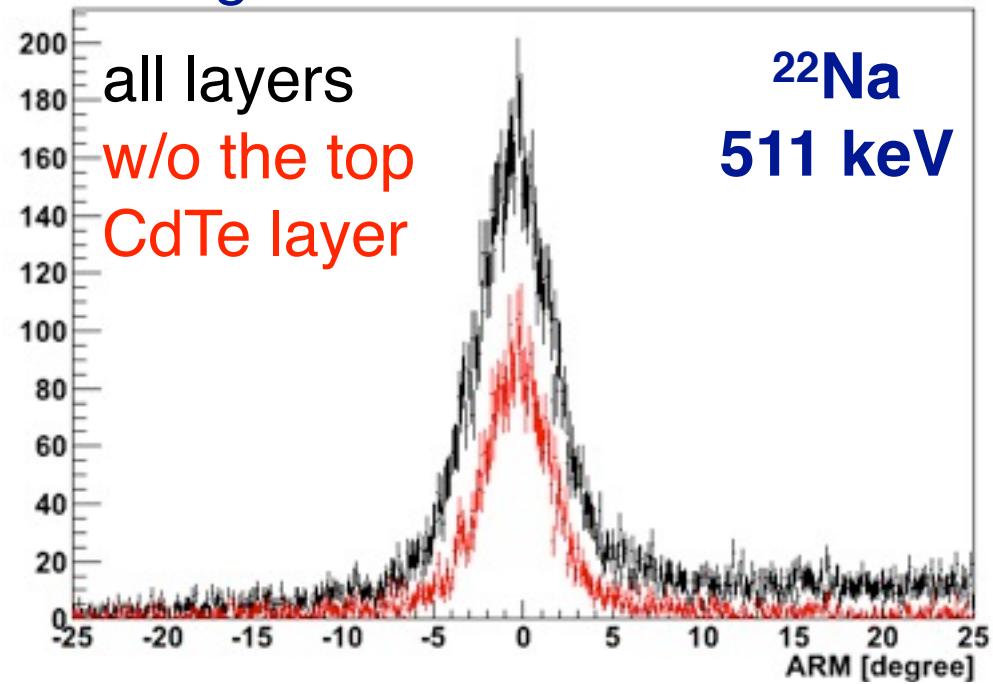
→ Use two-hit Compton events



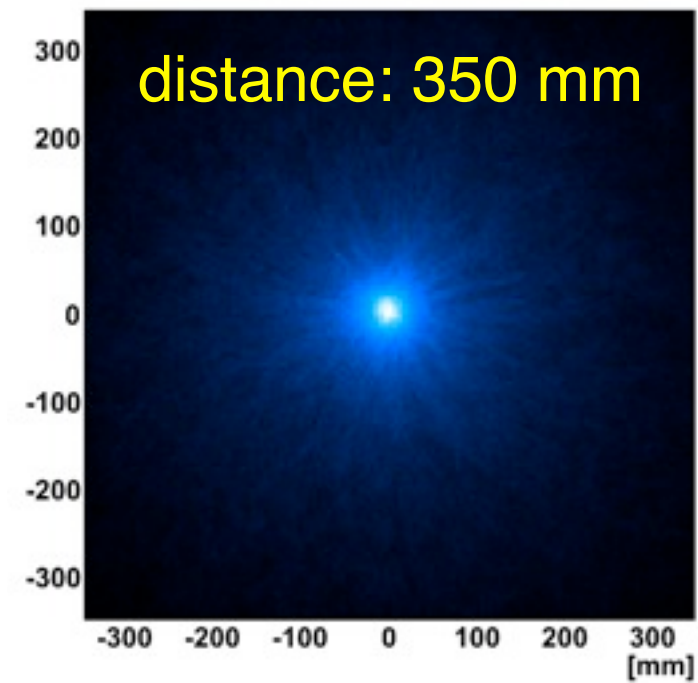
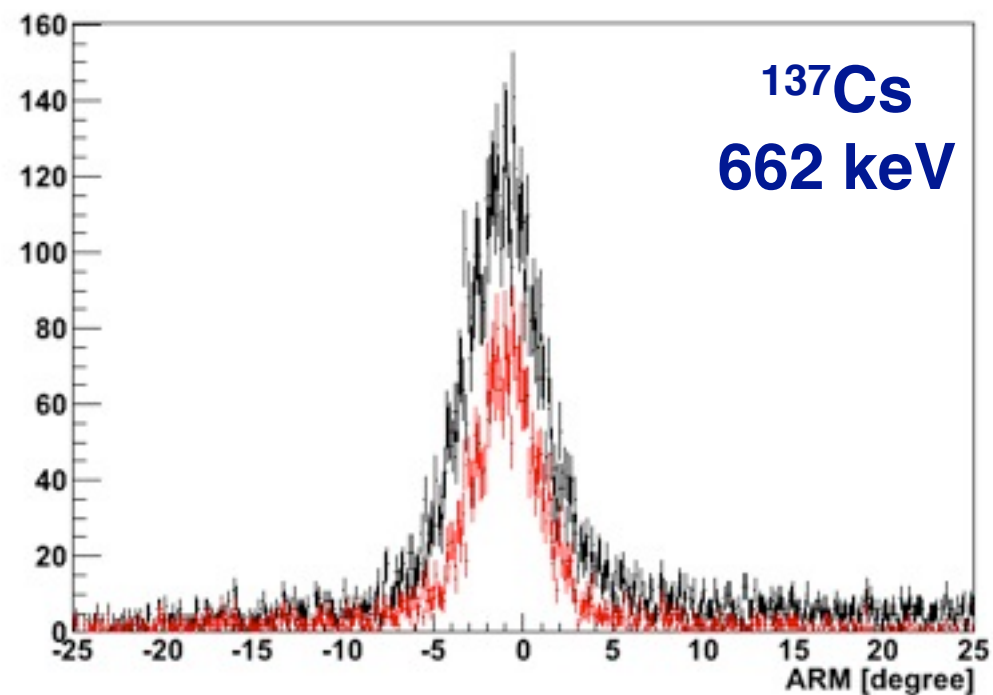
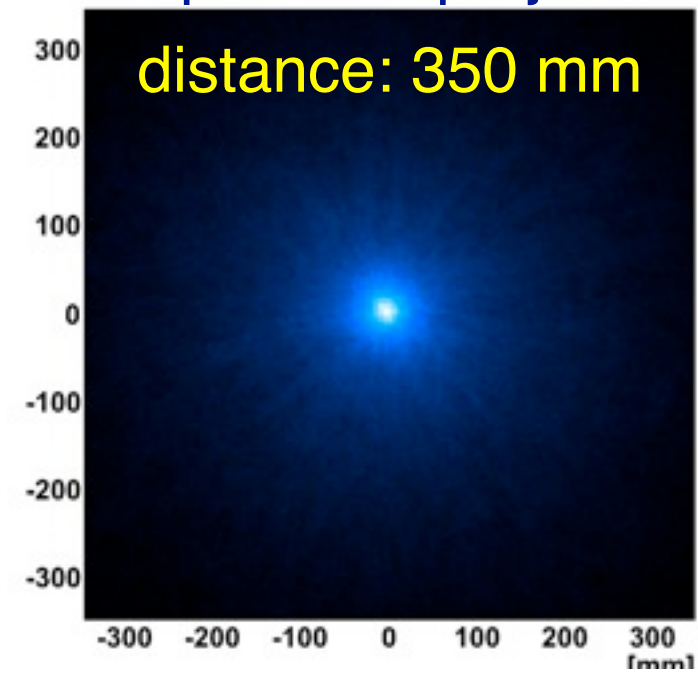
This method can be cross-checked by test pulses.
VATA 450/460 series has a function to operate calibration test pulses.

Initial Results

Angular resolution measure

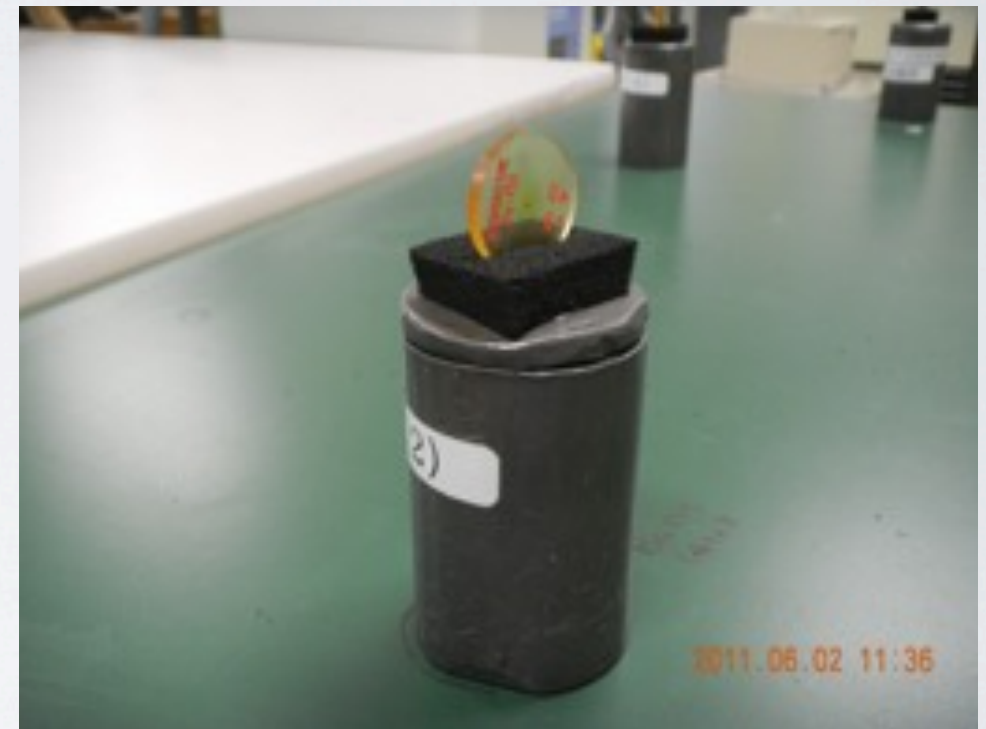
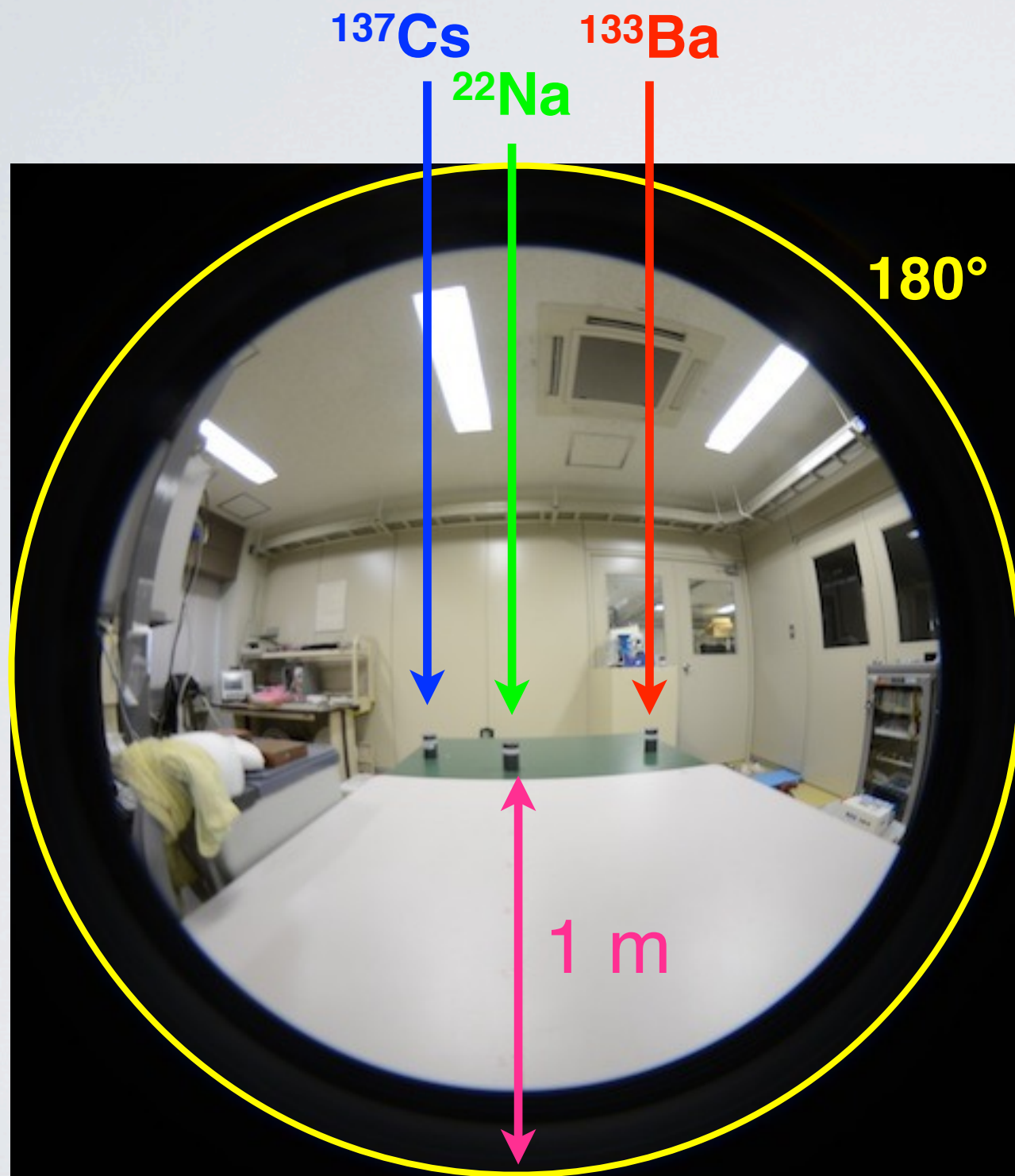


Simple back projection



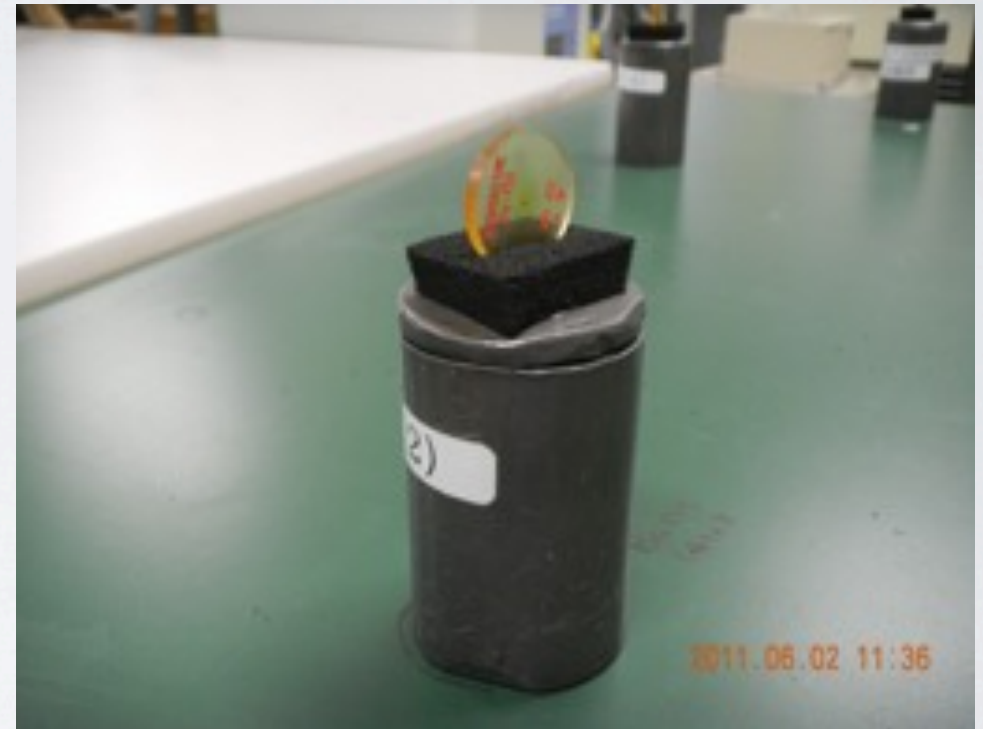
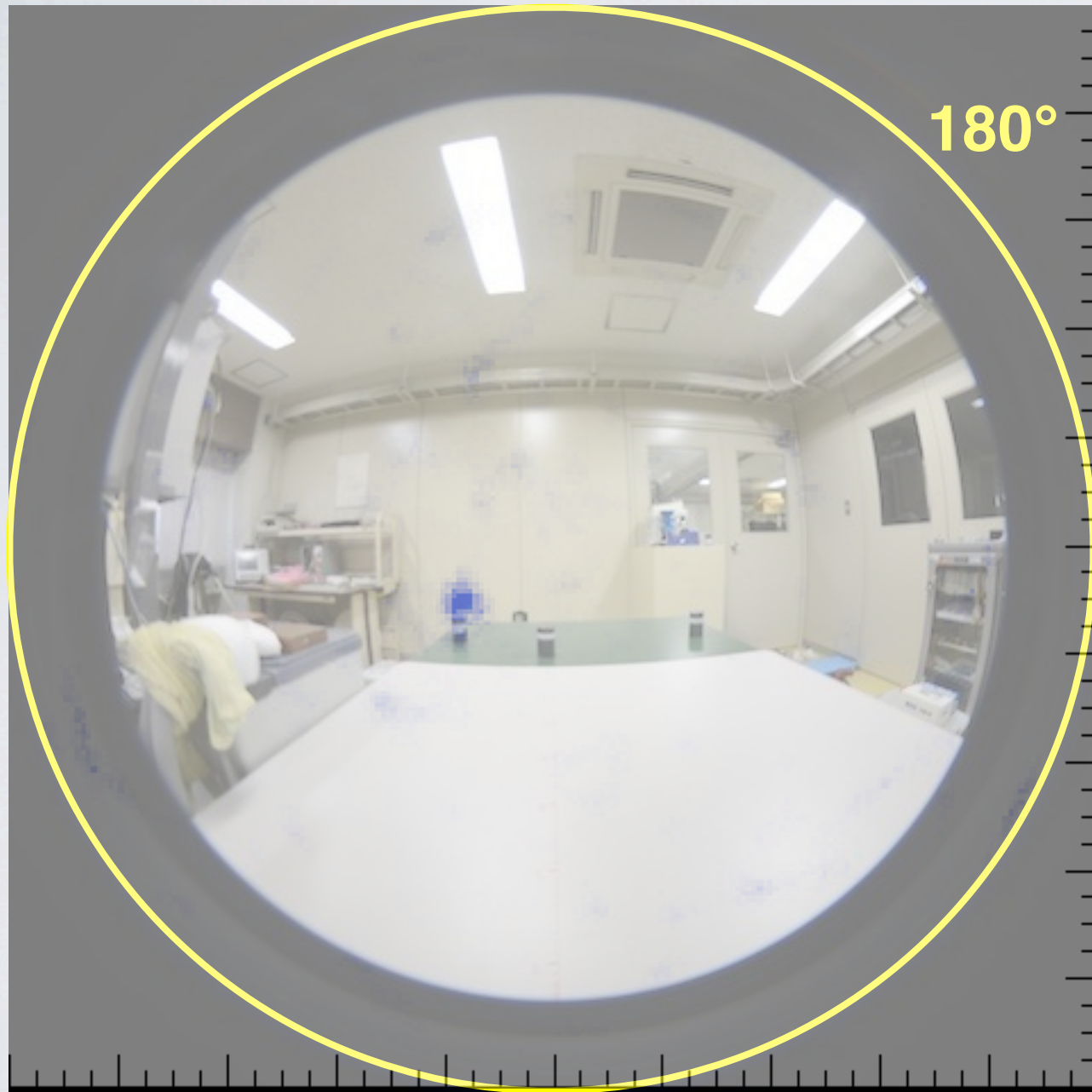
Angular resolution is 4-6 degrees, depending on event selection criteria.

Simultaneous Multi-RI Imaging



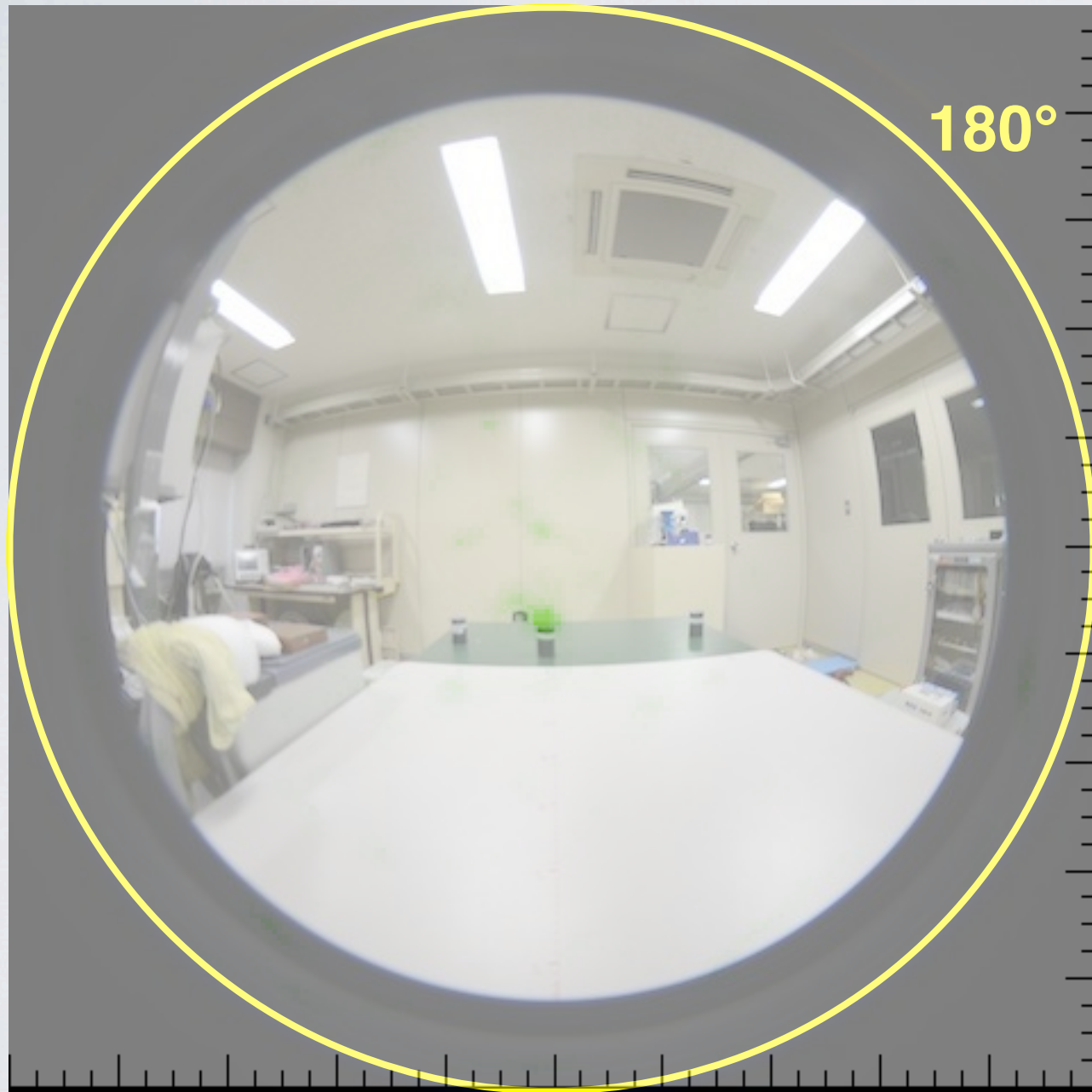
Simultaneous Multi-RI Imaging

^{137}Cs 662 keV (2.8 MBq)



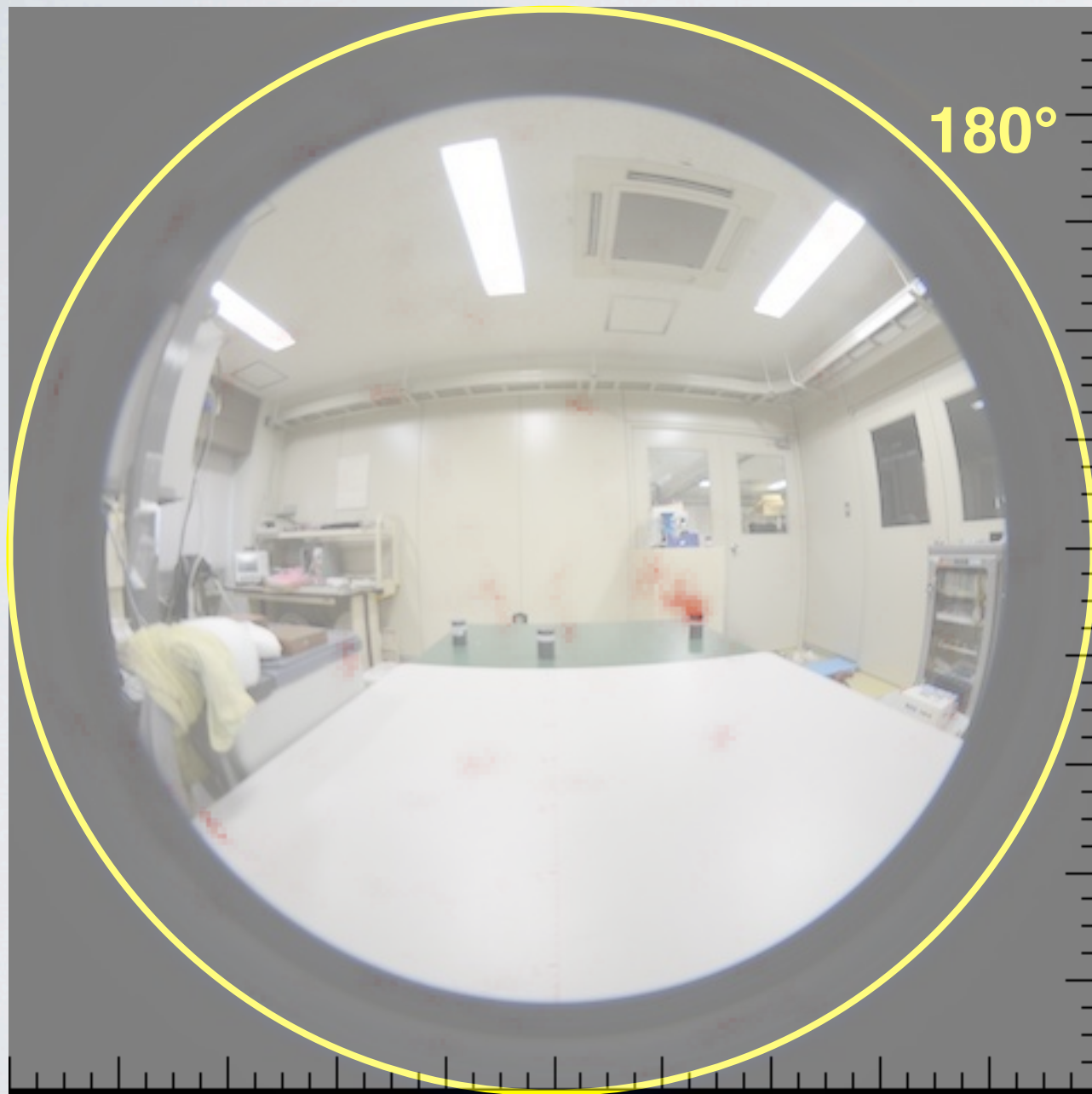
Simultaneous Multi-RI Imaging

^{22}Na 511 keV (0.5 MBq)



Simultaneous Multi-RI Imaging

^{133}Ba 356 keV (2.3 MBq)



We successfully obtained multi-RI gamma-ray images with the new camera.

Summary

- **Prototype camera**
 - ✓ **High-spatial resolution Compton imaging**
1 mm accuracy, better than 3 mm precision
 - ✓ **High-precision polarimetry**
degree of polarization $\sim 1\%$, angle $\sim 1^\circ$
- **New Si/CdTe module**
 - ✓ **Flexible and scalable structure**
 - ✓ **New ADC-included readout ASICs VATA 450/460/461**
 - ✓ **250-um-pitch double-sided strip detectors**
 - ✓ **High energy resolution CdTe-DSD: 1%**
 - ✓ **We demonstrated good Compton-imaging performance from the initial data analysis.**